

International IR Rectifier

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

PD - 95336A

IRF7910PbF

HEXFET® Power MOSFET

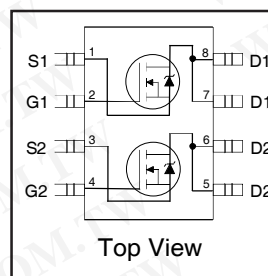
Applications

- High Frequency 3.3V and 5V input Point-of-Load Synchronous Buck Converters for Netcom and Computing Applications
- Power Management for Netcom, Computing and Portable Applications
- Lead-Free

Benefits

- Ultra-Low Gate Impedance
- Very Low $R_{DS(on)}$
- Fully Characterized Avalanche Voltage and Current

V_{DSS}	$R_{DS(on)}$ max	I_D
12V	15mΩ @ $V_{GS} = 4.5V$	10A



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	12	V
V_{GS}	Gate-to-Source Voltage	± 12	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	10	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	7.9	
I_{DM}	Pulsed Drain Current①	79	
$P_D @ T_A = 25^\circ C$	Maximum Power Dissipation④	2.0	W
$P_D @ T_A = 70^\circ C$	Maximum Power Dissipation④	1.3	W
	Linear Derating Factor	16	mW/°C
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	—	42	°C/W
$R_{\theta JA}$	Junction-to-Ambient ④	—	62.5	

Notes ① through ④ are on page 8
www.irf.com

IRF7910PbF

International
IR Rectifier

Static @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	12	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.01	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	11.5	15	mΩ	V _{GS} = 4.5V, I _D = 8.0A ③
		—	20	50		V _{GS} = 2.8V, I _D = 5.0A
V _{GS(th)}	Gate Threshold Voltage	0.6	—	2.0	V	V _{DS} = V _{GS} , I _D = 250μA
I _{DSS}	Drain-to-Source Leakage Current	—	—	100	μA	V _{DS} = 9.6V, V _{GS} = 0V
		—	—	250		V _{DS} = 9.6V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	V _{GS} = 12V
	Gate-to-Source Reverse Leakage	—	—	-200		V _{GS} = -12V

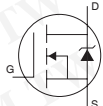
Dynamic @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g _{fs}	Forward Transconductance	18	—	—	S	V _{DS} = 6.0V, I _D = 8.0A
Q _g	Total Gate Charge	—	17	26	nC	I _D = 8.0A
Q _{gs}	Gate-to-Source Charge	—	4.4	—		V _{DS} = 6.0V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	5.2	—		V _{GS} = 4.5V
Q _{oss}	Output Gate Charge	—	16	—		V _{GS} = 0V, V _{DS} = 10V
t _{d(on)}	Turn-On Delay Time	—	9.4	—	ns	V _{DD} = 6.0V
t _r	Rise Time	—	22	—		I _D = 8.0A
t _{d(off)}	Turn-Off Delay Time	—	16	—		R _G = 1.8Ω
t _f	Fall Time	—	6.3	—		V _{GS} = 4.5V ③
C _{iss}	Input Capacitance	—	1730	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	1340	—		V _{DS} = 6.0V
C _{rss}	Reverse Transfer Capacitance	—	330	—		f = 1.0MHz

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy②	—	100	mJ
I _{AR}	Avalanche Current①	—	8.0	A

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	1.8	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	79		
V _{SD}	Diode Forward Voltage	—	0.85	1.3	V	T _J = 25°C, I _S = 8.0A, V _{GS} = 0V ③
		—	0.70	—		T _J = 125°C, I _S = 8.0A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	50	75	ns	T _J = 25°C, I _F = 8.0A, V _R = 12V
Q _{rr}	Reverse Recovery Charge	—	60	90	nC	di/dt = 100A/μs ③
t _{rr}	Reverse Recovery Time	—	51	77	ns	T _J = 125°C, I _F = 8.0A, V _R = 12V
Q _{rr}	Reverse Recovery Charge	—	60	90	nC	di/dt = 100A/μs ③

International
IR Rectifier

IRF7910PbF

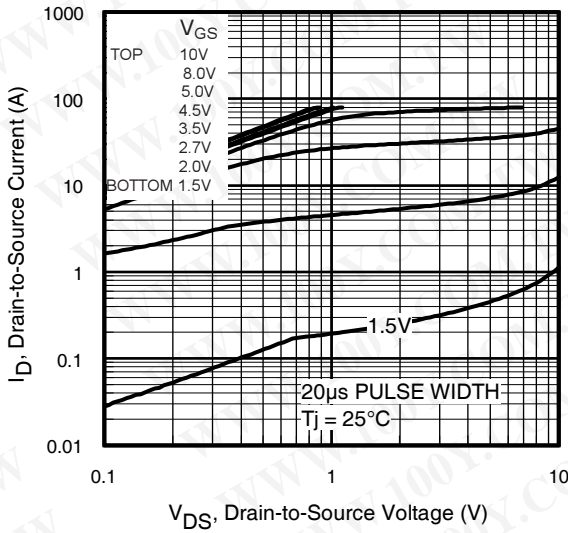


Fig 1. Typical Output Characteristics

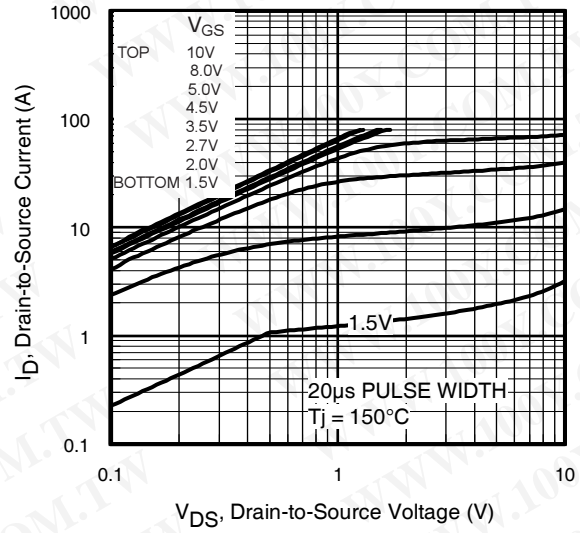


Fig 2. Typical Output Characteristics

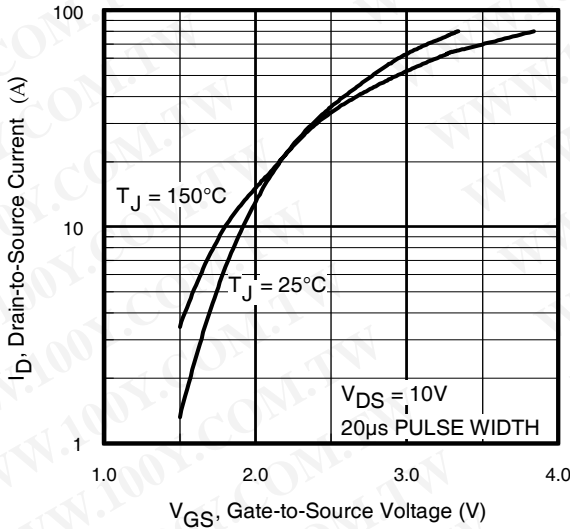


Fig 3. Typical Transfer Characteristics

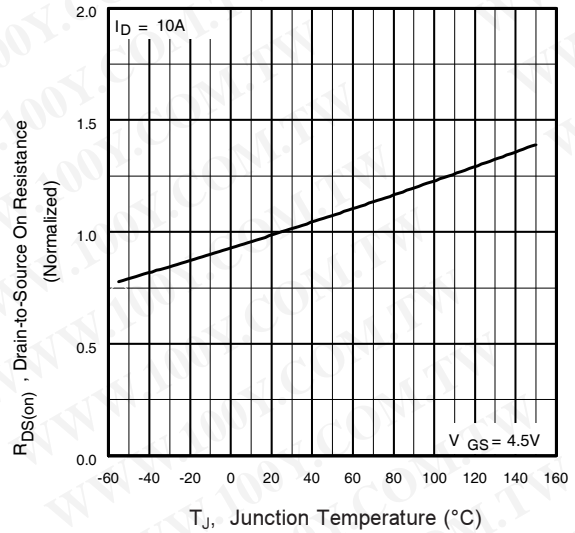


Fig 4. Normalized On-Resistance Vs. Temperature

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

IRF7910PbF

International
IR Rectifier

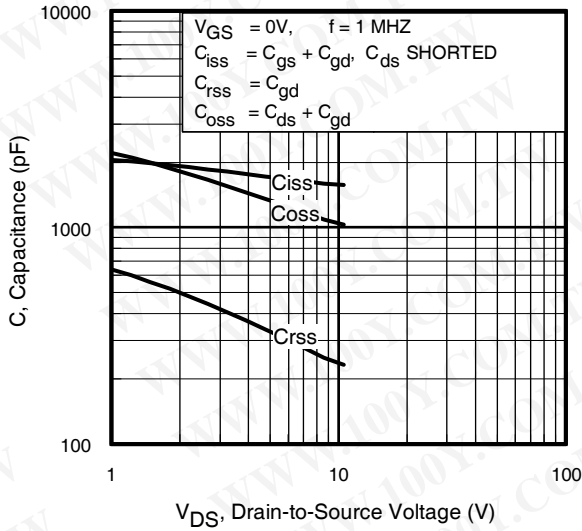


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

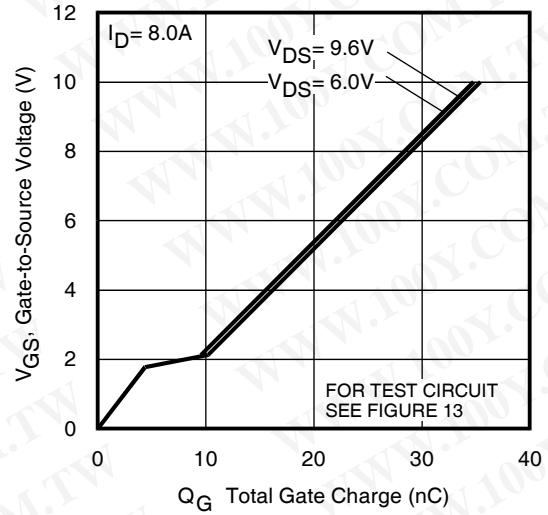


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

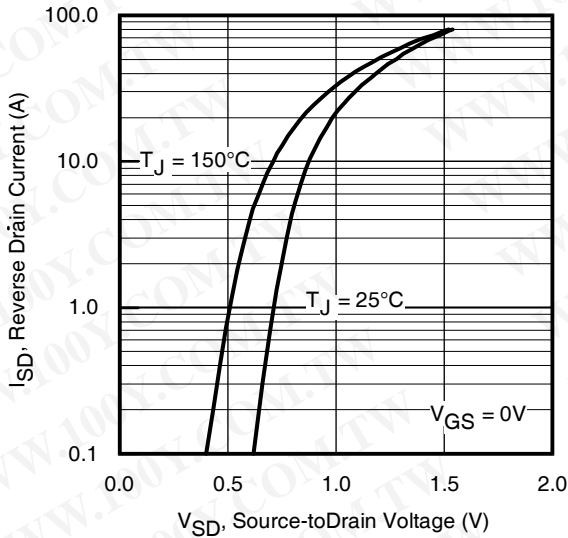


Fig 7. Typical Source-Drain Diode Forward Voltage

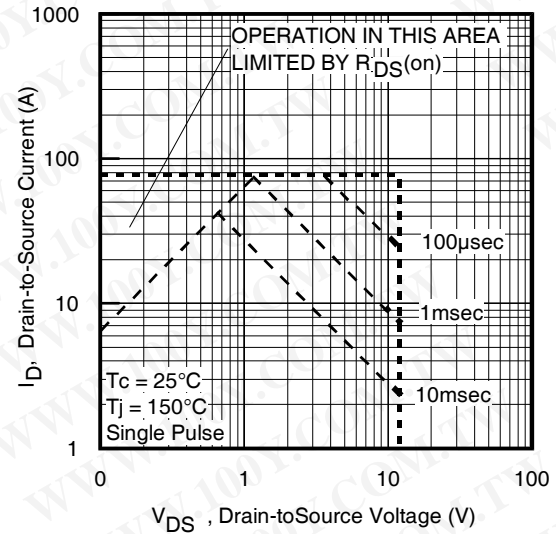


Fig 8. Maximum Safe Operating Area

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
 Http://www.100y.com.tw

International
IR Rectifier

IRF7910PbF

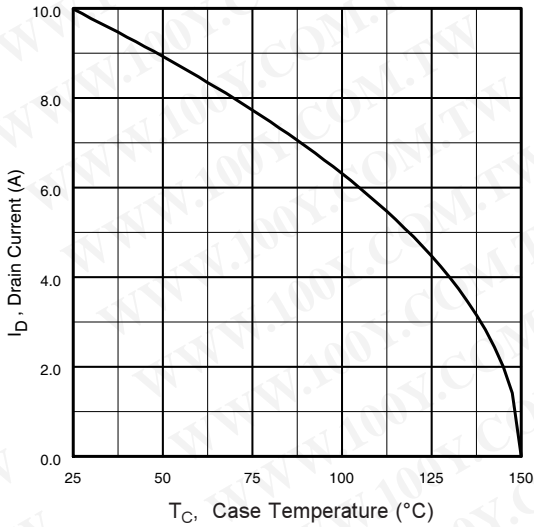


Fig 9. Maximum Drain Current Vs. Ambient Temperature

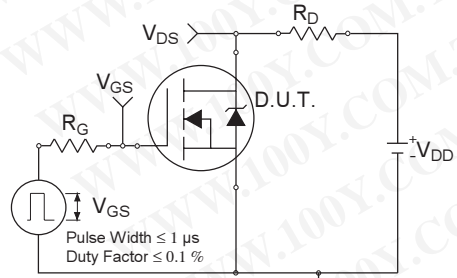


Fig 10a. Switching Time Test Circuit

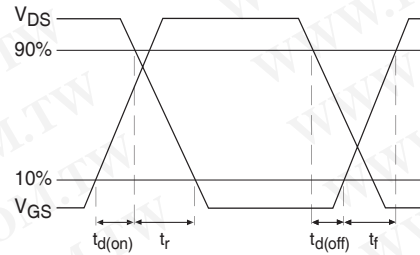


Fig 10b. Switching Time Waveforms

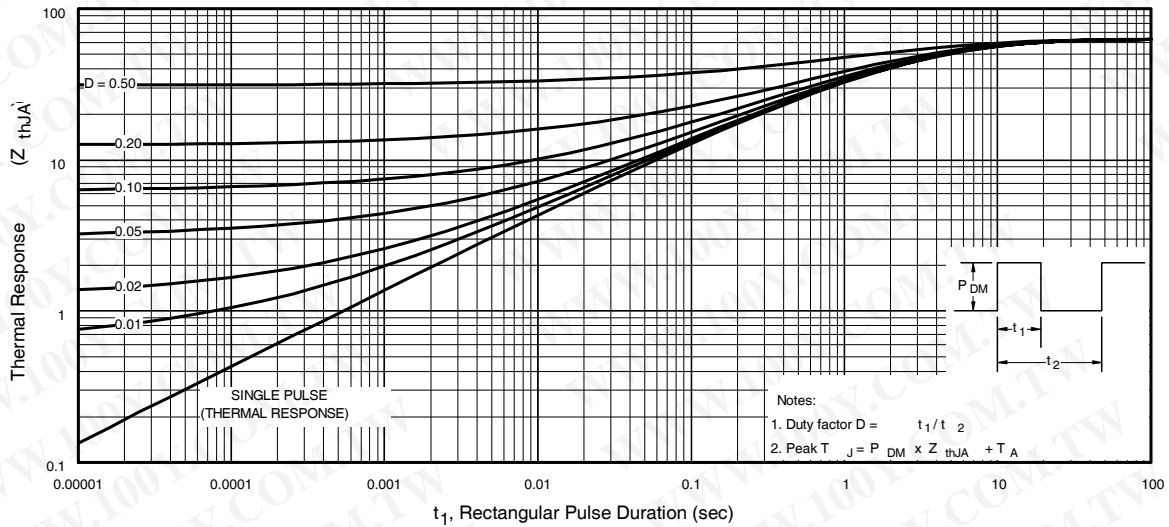


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

IRF7910PbF

International
IRF Rectifier

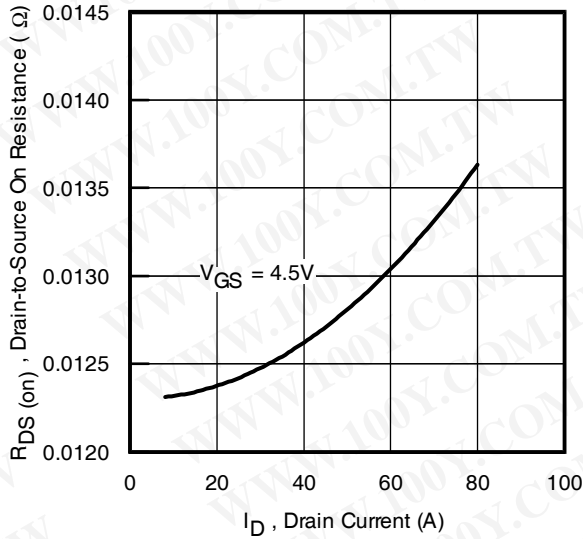


Fig 12. On-Resistance Vs. Drain Current

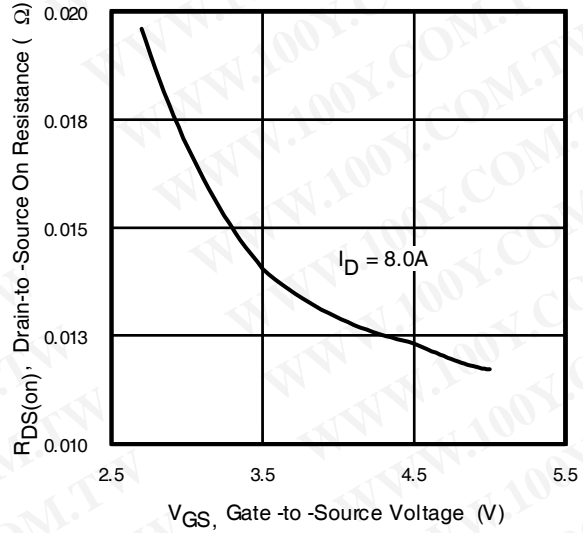


Fig 13. On-Resistance Vs. Gate Voltage

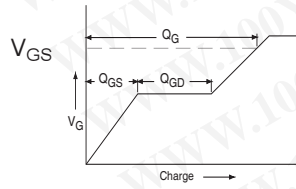
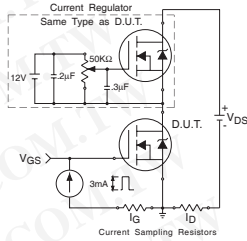


Fig 14a&b. Basic Gate Charge Test Circuit and Waveform

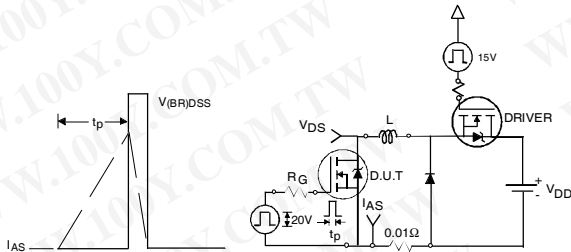


Fig 15a&b. Unclamped Inductive Test circuit and Waveforms

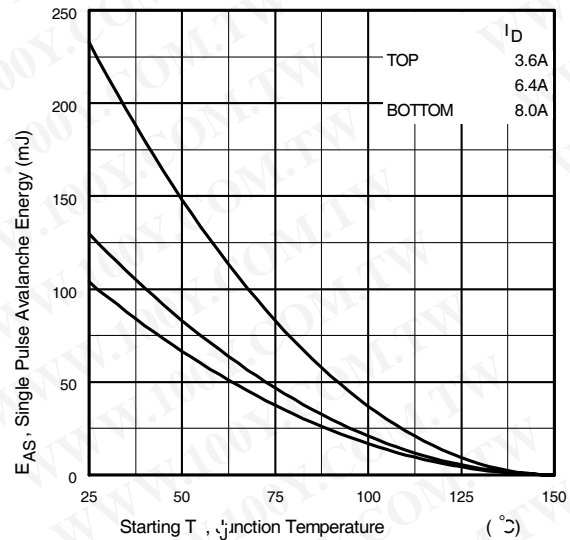


Fig 15c. Maximum Avalanche Energy Vs. Drain Current

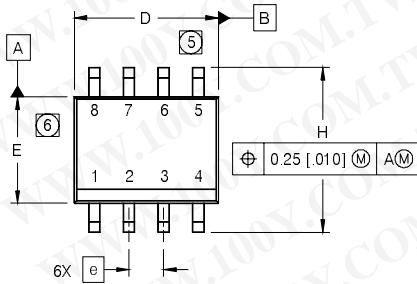
勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

International
IR Rectifier

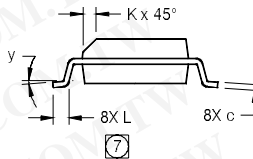
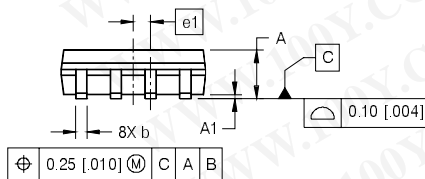
IRF7910PbF

SO-8 Package Outline (MOSFET & Fetky)

Dimensions are shown in millimeters (inches)



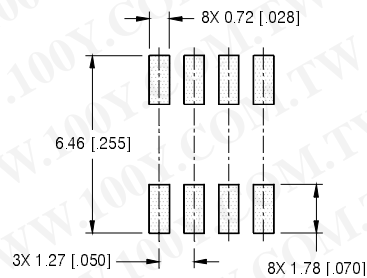
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



NOTES:

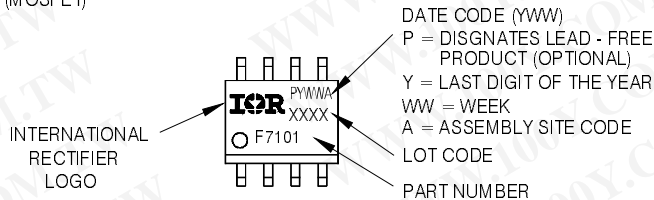
- DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- CONTROLLING DIMENSION: MILLIMETER
- DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



SO-8 Part Marking Information

EXAMPLE: THIS IS AN IRF7101 (MOSFET)



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>
www.irf.com

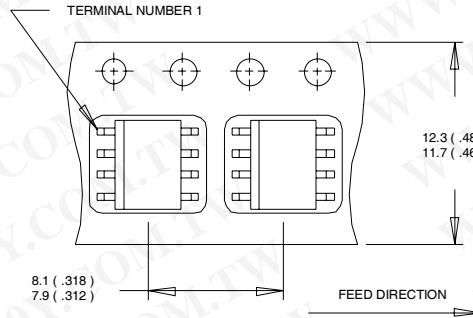
勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

IRF7910PbF

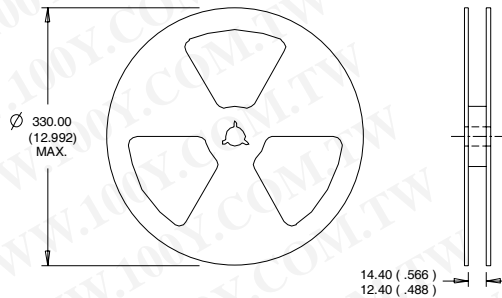
SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)

International
IR Rectifier



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 3.2\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 8.0\text{A}$.
- ③ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board, $t < 10$ sec

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Consumer market.
 Qualifications Standards can be found on IR's Web site.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
 TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.07/2008

www.irf.com